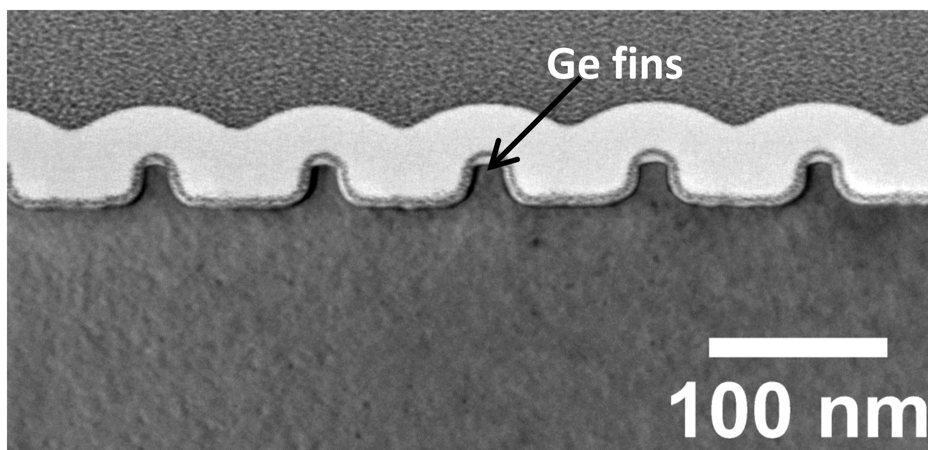
Coláiste na hOllscoile Corcaigh, Éire
University College Cork, Ireland

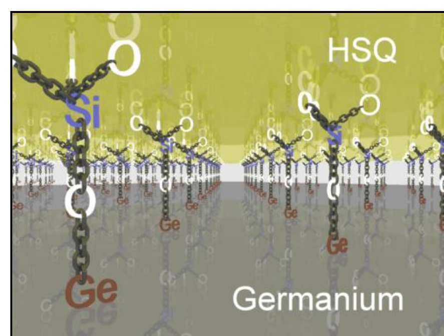
CRANN

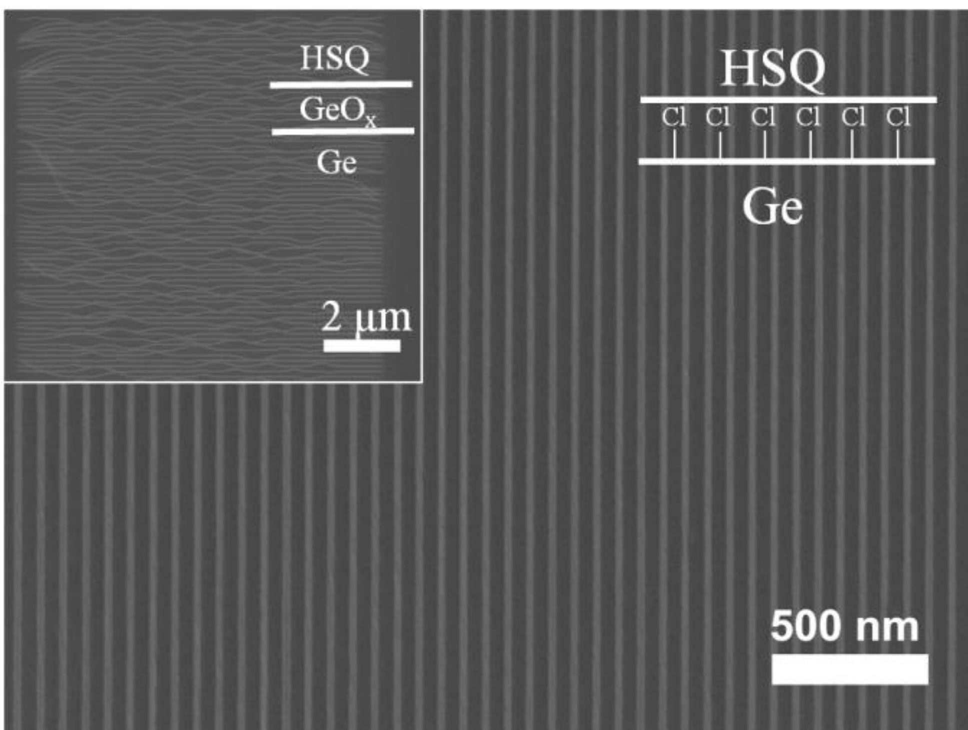
High Resolution Lithography for Germanium

Images



The HSQ line pattern can be transferred to the Ge substrate allowing production of Ge nanofin arrays.





EBL using HSQ resist on GeO_x results in delamination of HSQ lines during immersion in developer solution. Removal of GeO_x and chlorination of the Ge crystal enables straight sub-20 nm HSQ line structures on Ge.

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